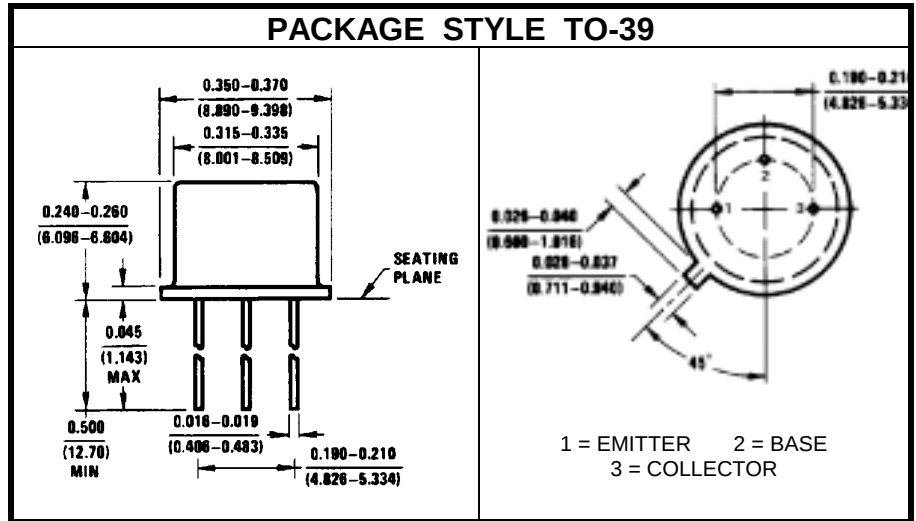


SILICON NPN RF POWER TRANSISTOR

DESCRIPTION: The **MRF237** is designed for large signal power amplifier applications operating to 225 MHz

MAXIMUM RATINGS

I_C	1.0 A
V_{CB0}	36 V
V_{CEO}	18 V
P_{DISS}	8.0 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+200^\circ\text{C}$
θ_{JC}	22 $^\circ\text{C/W}$



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 10\text{ mA}$	18			V
BV_{CES}	$I_C = 5.0\text{ mA}$	36			V
BV_{EBO}	$I_C = 1.0\text{ mA}$	4.0			V
I_{CBO}	$V_{CE} = 15\text{ V}$			.25	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 250\text{ mA}$	5.0			---
C_{OB}	$V_{CB} = 15\text{ V}$ $f = 1.0\text{ MHz}$		15	20	pF
G_{PE}	$V_{CC} = 12.5\text{ V}$ $P_{OUT} = 4.0\text{ W}$ $f = 175\text{ MHz}$	12	14		dB
η		50	62		%